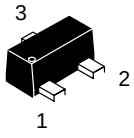
Bias Resistor Transistor

NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

LDTC113ZET1G
S-LDTC113ZET1G



SC-89

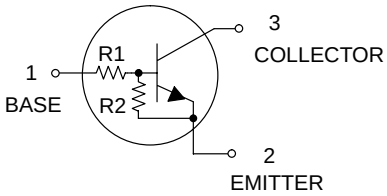
- **Applications**

  Inverter, Interface, Driver

- **Features**

1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
		LDTC113ZET1G	
Supply voltage	V_{CC}	50	V
Input voltage	V_{IN}	–5 to +10	V
Output current	I_O	100	mA
	$I_{C(Max.)}$	100	
Power dissipation	P_D	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTC113ZET1G S-LDTC113ZET1G	N7	1	10	3000/Tape & Reel
LDTC113ZET3G S-LDTC113ZET3G	N7	1	10	10000/Tape & Reel

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$	–	–	0.3	V	V_{CC}=5V, I_O=100μA
	$V_{I(on)}$	3	–	–		V_O=0.3V, I_O=20mA
Output voltage	$V_{O(on)}$	–	0.1	0.3	V	I_O/I_I=10mA/0.5mA
Input current	I_I	–	–	7.2	mA	V_I=5V
Output current	$I_{O(off)}$	–	–	0.5	μA	V_{CC}=50V, V_I=0V
DC current gain	G_I	33	–	–	–	V_O=5V, I_O=5mA
Input resistance	R_1	0.7	1	1.3	kΩ	–
Resistance ratio	R_2/R_1	8	10	12	–	–
Transition frequency	f_T *	–	250	–	MHz	V_{CE}=10V, I_E= –5mA, f=100MHz

* Characteristics of built-in transistor

LDTC113ZET1G ;S-LDTC113ZET1G

- **Electrical characteristic curves**

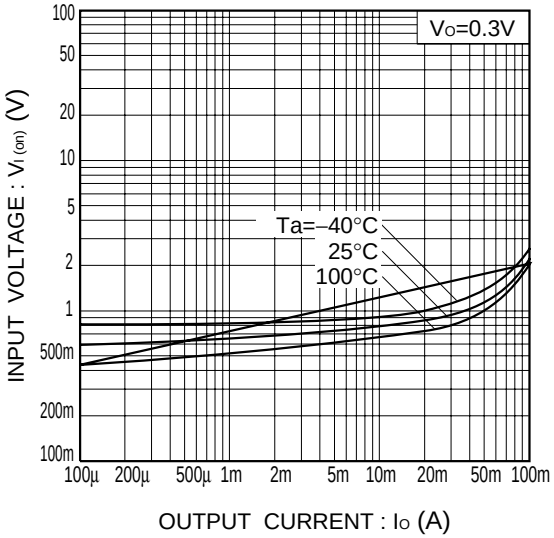


Fig.1 Input voltage vs. output current (ON characteristics)

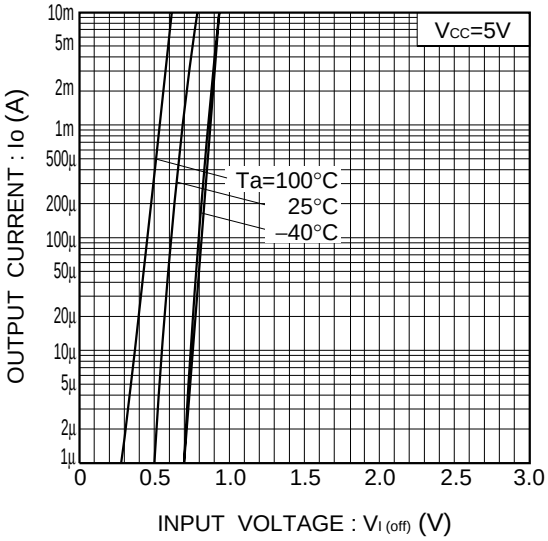


Fig.2 Output current vs. input voltage (OFF characteristics)

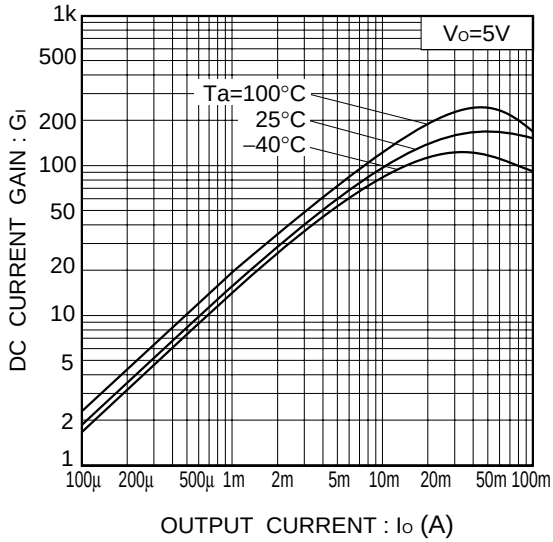


Fig.3 DC current gain vs. output current

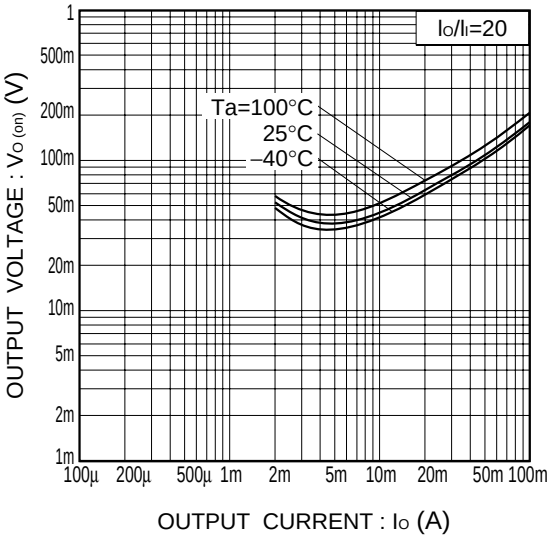
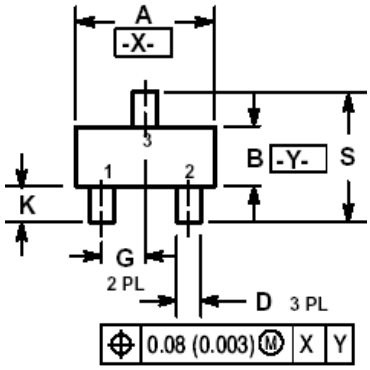


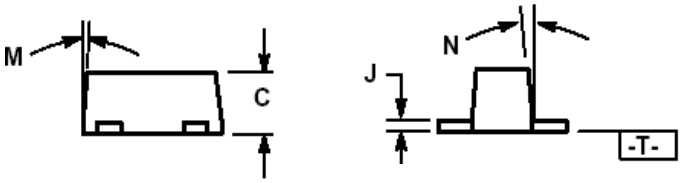
Fig.4 Output voltage vs. output current

LDTC113ZET1G ;S-LDTC113ZET1G

SC-89



NOTES:
1.DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2.CONTROLLING DIMENSION: MILLIMETERS
3.MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4.463C-01 OBSOLETE, NEW STANDARD 463C-02.



	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067